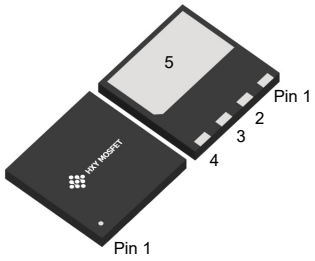
HC1D06065L

Silicon Carbide Schottky Diode

General Description

This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.



DFN8X8B

Features

- Low conduction loss due to low V_F
- Extremely low switching loss by tiny Q_C
- Highly rugged due to better surge current
- Industrial standard quality and reliability

Applications

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction

Ordering Part Number	Package	Marking
HC1D06065L	DFN8X8B	HC1D06065L

Maximum Ratings (at Tc = 25 °C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	650	V
Surge Peak Reverse Voltage	V_{RSM}	650	V
DC Peak Reverse Voltage	V_R	650	V
Continuous Forward Current T_C = 25°C T_C = 135°C T_C = 162°C	I_F	 23 12 6	A
Repetitive Peak Forward Surge Current T_C = 25°C,t_p=10ms,Half Sine Pulse T_C = 110°C,t_p=10ms,Half Sine Pulse	I_{FRM}	 28 17	A
Non-Repetitive Forward Surge Current T_C = 25°C,t_p=10ms,Half Sine Pulse T_C = 110°C,t_p=10ms,Half Sine Pulse	I_{FSM}	 48 43	A
i^2dt value T_C = 25°C,t_p=10ms,Half Sine Pulse T_C = 110°C,t_p=10ms,Half Sine Pulse	$\int i^2dt$	 11.4 9.1	A^2s
Power dissipation T_C = 25°C T_C = 110°C	P_{tot}	 71 30	W
Operating junction Range	T_j	-55 to +175	°C
Storage temperature Range	T_{stg}	-55 to +150	°C

Thermal Resistance

Parameter	Symbol	Typ.	Unit
Thermal resistance, junction – case.	R_{thJC}	2.1	°C/W

Electrical Characteristic (at Tc = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Forward Voltage	V_F	-	1.3	1.5	V	I_F=6A, T_j=25°C
		-	1.5			T_j=175°C
Reverse Current	I_R	-	-	50	μA	V_R=650V, T_j=25°C
		-	-	200		T_j=175°C
Total Capacitive Charge	Q_C	-	18	-	nC	V_R=400V，T_j=25℃ $Q_C = \int_0^{V_R} C(V)dV$
Total Capacitance	C	-	358	-	pF	T_j=25℃, f=1MHz, V_R=0V
		-	36	-		V_R=200V
		-	30	-		V_R=400V

Characteristics Curve

Fig 1: Forward Characteristics

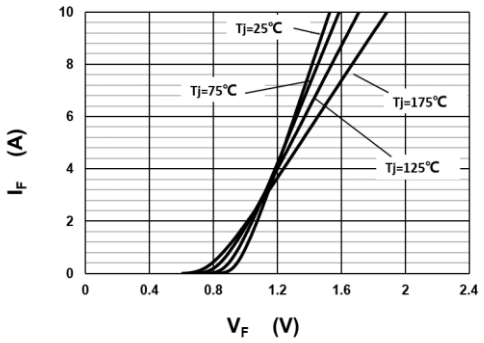


Fig 2: Reverse Characteristics

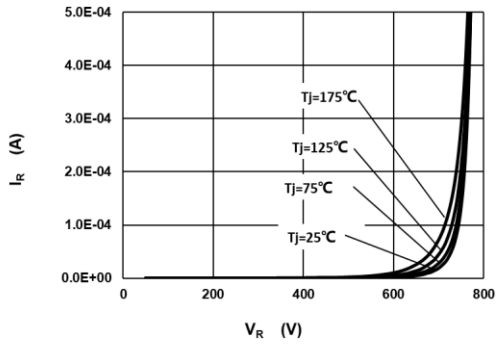


Fig 3: Current Derating

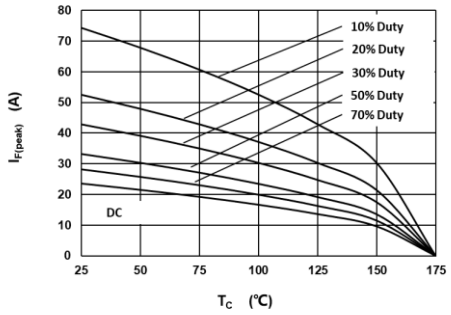


Fig 4: Power Derating

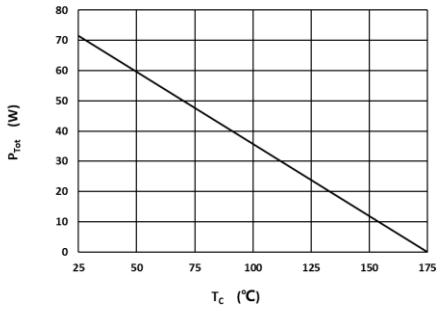


Fig 5: Capacitance vs. Reverse Voltage

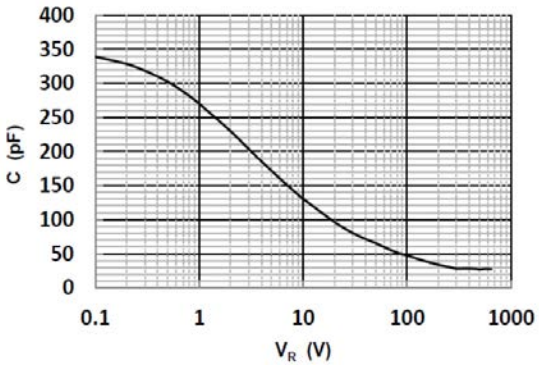


Fig 6: Reverse Charge vs. Reverse Voltage

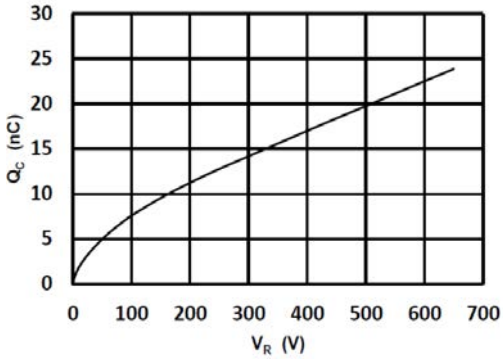


Fig 7: Typical Capacitance Stored Energy

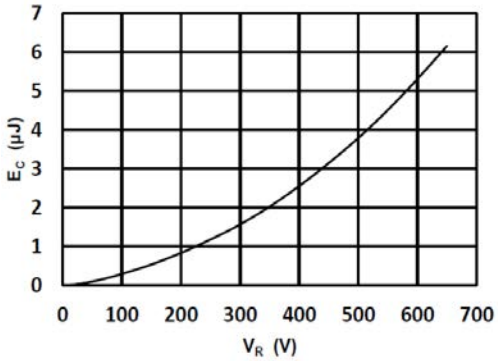
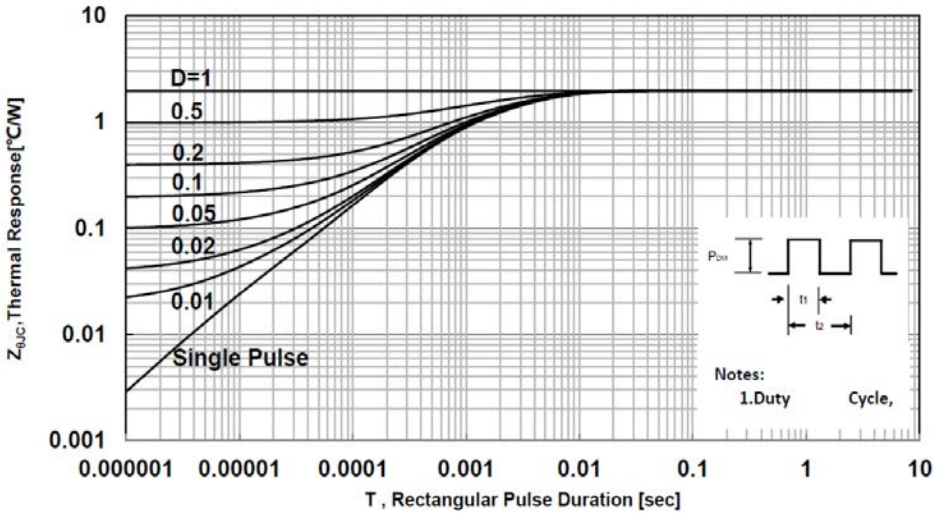
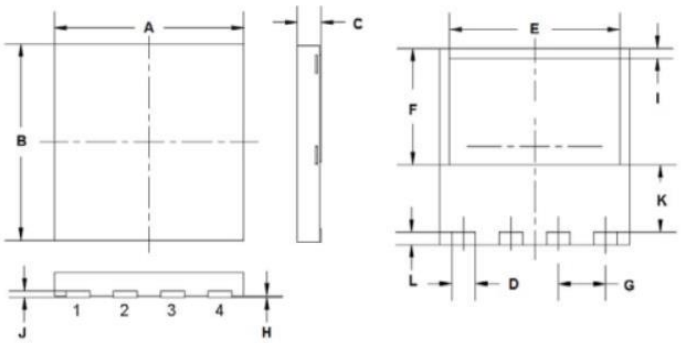


Fig 8: Transient Thermal Impandance



Package Dimensions

Package DFN8X8B



Unit: mm

Dimension	Min.	Max.
A	7.90	8.10
B	7.90	8.10
C	0.75	0.95
D	0.90	1.10
E	7.10	7.30
F	4.65	4.85
G	1.80	2.20
H	0.00	0.05
I	0.30	0.50
J	0.10	0.30
K	2.65	2.85
L	0.40	0.60

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